INTEGRATED CIRCUIT **TOSHIBA**

TECHNICAL DATA

TOSHIBA MOS DIGITAL INTEGRATED CIRCUIT TC5832 FT SILICON GATE CMOS

32 MBIT (4 M \times 8 BITS) CMOS NAND E²PROM

TENTATIVE DATA

DESCRIPTION

The TC5832FT device is a single 5.0-volt 33 M (34,603,008) bit NAND Electrically Erasable and Programmable Read Only Memory (NAND EEPROM) organized as 528 byte × 16 pages × 512 blocks. The device has a 528-byte, static register which allows the program and read data to be transferred between the register and the memory cell array in 528-byte increments. The Erase operation is implemented in a single block unit (8 kbytes + 256 bytes: 528 bytes × 16 pages).

The TC5832FT is a serial type of memory device which utilizes the I/O pins for both address and data input/output as well as command inputs. The Erase and Program operations are automatically executed, making the device most suitable for applications such as solid state file storage, voice recording, image file memory for still cameras and other systems which require high-density, and non-volatile memory data storage.

FEATURES

• Organization: Memory cell array: 528 × 8 k × 8

Register $: 528 \times 8$ Page size

: 528 byte : (8 k + 256) byte Block size

: Read, Reset, Auto Page Program Auto Block Erase, Suspend/Resume Mode

Status Read

Mode control: Serial input/output

Command control

400 mil TSOP Type II Package : 400 mil TSOP Type II TC5832FT: TSOP44-P-400B (Weight: 0.48 g typ) Power supply $: V_{CC} = 5.0 V \pm 0.5 V$

Access time

Cell array-Register: 10 \(\mu \max \)
Serial Read Cycle: 50 ns min

Operating current Read (50 ns cycle) : 15 mA typ Program (ave.) 40 mA typ 20 mA typ Erase (ave.) Standby : 100 µA

PIN ASSIGNMENT (TOP VIEW)

TC5832FT

			1
V _{SS}	1 2	44 43	□ V _{CC} □ C E
ALE	∃3	42	∃ ŘĒ :
WE	∃ 4	41	□ R/B :
WP	<u>∃</u> 5	40	□ OP
NC		39	□ NC
NC	日ž	38	Бис
NC	□8	37	□NC
NC	□ 9	36	□NC
NC	□ 10	35	□ ис
	11	34	
	12	33	
NC	□ 13	32	□ис
NC	□ 14	31	□ ис
NC	□ 15	30	□ ис
NC	□ 16	29	□ис
NC.	.닖.17.	28	<u> </u>
I/O 1	□ 18	27	□ 1/O 8
I/O 2	<u>⊣</u> 19	26	⊣ 1/07 :
I/O 3	월 20	25	<u> </u>
1/0 4	님21	24	⊣ 1/O 5 :
: V _{SS}	니.22	23	∐.V.cc.
		·	•

PIN NAMES

I/O _{1 to 8}	I/O Port	
CE	Chip Enable	
WE	Write Enable	
RE	Read Enable	
CLE	Command Latch Enable	
ALE	Address Latch Enable	
WP	Write Protect	
R/B	Ready/Busy	
ОР	Option Pin	
V _{CC}	Power Supply	
V _{SS}	Ground	

OP: GND Input: 528 Byte/Page Operation V_{CC} Input : 512 Byte/Page Operation

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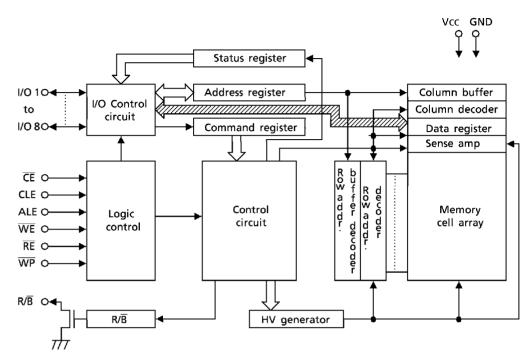
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TC5832 FT

BLOCK DIAGRAM



ABSOLUTE MAXIMUM RATINGS

SYMBOL	RATING	VALUE	UNIT	
V _{CC}	Power Supply	- 0.6 to 7.0	V	
V_{IN}	Input Voltage	- 0.6 to 7.0	V	
V _{I/O}	Input/Output Voltage	- 0.6 V to Vcc + 0.5 V (≦ 7.0 V)	V	
P _D	Power Dissipation	0.5	W	
T _{SOLDER}	Soldering Temperature (10 s)	260	°C	
T _{STG}	Storage Temperature	– 55 to 150	°C	
T _{OPR}	Operating Temperature	0 to 70	°C	

CAPACITANCE *(Ta = 25°C, f = 1 MHz)

SYMBOL	PARAMETER	CONDITION	MIN	TYP	MAX	UNIT
C _{IN}	Input	$V_{IN} = 0 V$	ı	5	10	РF
C _{OUT}	Output	V _{OUT} = 0 V	ı	5	10	РF

^{*} This parameter is periodically sampled and is not tested for every component.

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